

SEMICONDUCTOR DEVICE AND PROCESS OF PRODUCTION OF SAME

ABSTRACT OF THE DISCLOSURE

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A semiconductor device comprising: a first insulating film formed on a semiconductor substrate; a semiconductor layer at least a part of which is formed on the first insulating film; a second insulating film comprising a non-doped silicon oxide film and formed on the semiconductor layer; a third insulating film comprising a silicon oxide film containing at least phosphorus formed on the second insulating film; and a fourth insulating film comprising a non-doped silicon oxide film formed on the third insulating film.

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